

Linear Systems High Voltage Super-Beta Monolithic Dual NPN

The LS302 is a monolithic pair of high voltage Super-Beta NPN transistors mounted in a single P-DIP package. The monolithic dual chip design reduces parasitics and gives better performance while ensuring extremely tight matching.

The 8 Pin P-DIP provides ease of manufacturing, and the symmetrical pinout prevents improper orientation.

(See Packaging Information).

LS302 Features:

- Very high gain
- Tight matching
- Low Output Capacitance

FEATURES

HIGH GAIN	$h_{FE} \geq 1000$ @ $1\mu A$ TYP.
LOW OUTPUT CAPACITANCE	$C_{OBO} \leq 2.0pF$
TIGHT V_{BE} MATCHING	$ V_{BE1} - V_{BE2} = 0.2mV$ TYP.
HIGH f_t	100MHZ

ABSOLUTE MAXIMUM RATINGS¹ @ 25°C (unless otherwise noted)

Maximum Temperatures

Storage Temperature	-65°C to +200°C
Operating Junction Temperature	-55°C to +150°C

Maximum Power Dissipation

Continuous Power Dissipation (One side)	250mW
Continuous Power Dissipation (Both sides)	500mW
Linear Derating factor (One side)	2.3mW/°C
Linear Derating factor (Both sides)	4.3mW/°C

Maximum Currents

Collector Current	5mA
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MATCHING CHARACTERISTICS @ 25°C (unless otherwise stated)

SYMBOL	CHARACTERISTIC	MIN	TYP	MAX	UNITS	CONDITIONS
$ V_{BE1} - V_{BE2} $	Base Emitter Voltage Differential	--	0.2	1	mV	$I_C = 10\mu A, V_{CE} = 5V$
$\Delta V_{BE1} - V_{BE2} / \Delta T$	Base Emitter Voltage Differential Change with Temperature	--	1	5	$\mu V/^\circ C$	$I_C = 10\mu A, V_{CE} = 5V$ $T_A = -55^\circ C$ to $+125^\circ C$
$ I_{B1} - I_{B2} $	Base Current Differential	--	1	5	nA	$I_C = 10\mu A, V_{CE} = 5V$
h_{FE1} / h_{FE2}	DC Current Gain Differential	--	5	--	%	$I_C = 10\mu A, V_{CE} = 5V$

ELECTRICAL CHARACTERISTICS @ 25°C (unless otherwise noted)

SYMBOL	CHARACTERISTICS	MIN.	TYP.	MAX.	UNITS	CONDITIONS
BV_{CBO}	Collector to Base Voltage	35	--	--	V	$I_C = 10\mu A, I_E = 0$
BV_{CEO}	Collector to Emitter Voltage	35	--	--	V	$I_C = 10\mu A, I_B = 0$
BV_{EBO}	Emitter-Base Breakdown Voltage	6.2	--	--	V	$I_E = 10\mu A, I_C = 0^2$
BV_{CCO}	Collector to Collector Voltage	100	--	--	V	$I_C = 10\mu A, I_E = 0$
h_{FE}	DC Current Gain	--	1000	--		$I_C = 1\mu A, V_{CE} = 5V$
		1000	--	--		$I_C = 10\mu A, V_{CE} = 5V$
		--	1000	--		$I_C = 500\mu A, V_{CE} = 5V$
$V_{CE(SAT)}$	Collector Saturation Voltage	--	--	0.5	V	$I_C = 1mA, I_B = 0.1mA$
I_{EBO}	Emitter Cutoff Current	--	--	0.2	pA	$I_C = 0, V_{EB} = 3V$
I_{CBO}	Collector Cutoff Current	--	--	100	pA	$I_E = 0, V_{CB} = 10V$
C_{OBO}	Output Capacitance	--	--	2	pF	$I_E = 0, V_{CB} = 1V$
C_{C1C2}	Collector to Collector Capacitance	--	--	2	pF	$V_{CC} = 0V$
I_{C1C2}	Collector to Collector Leakage Current	--	--	0.5	nA	$V_{CC} = \pm 80V$
f_T	Current Gain Bandwidth Product	100	--	--	MHz	$I_C = 200\mu A, V_{CE} = 5V$
NF	Narrow Band Noise Figure	--	--	3	dB	$I_C = 10\mu A, V_{CE} = 3V, BW=200Hz, R_G = 10K\Omega, f = 1KHz$

Notes:

1. Absolute Maximum ratings are limiting values above which serviceability may be impaired

2. The reverse base-to-emitter voltage must never exceed 6.2 volts; the reverse base-to-emitter current must never exceed $10\mu A$.



Available Packages:

LS302 in P-DIP

LS302 available as bare die

Please contact Micross for full package and die dimensions:

Email: chipcomponents@micross.com

Web: www.micross.com/distribution.aspx

P-DIP (Top View)

